

Silicon NPN Power Transistors

2SC2706

DESCRIPTION

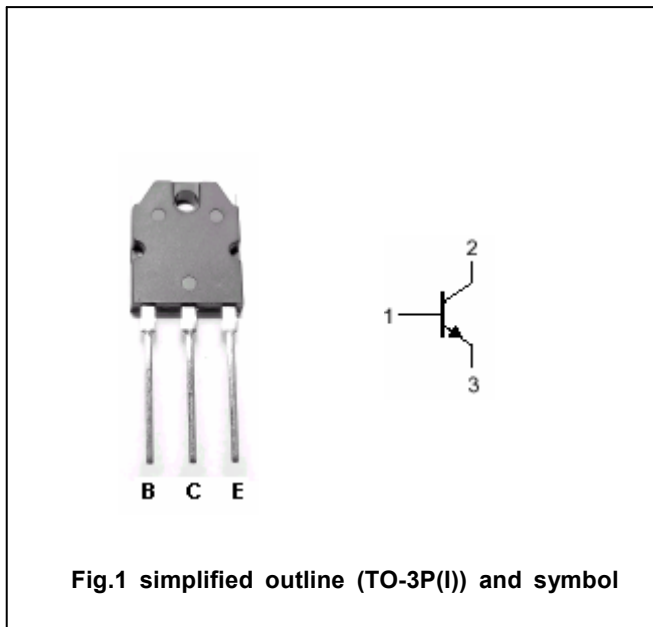
- With TO-3P(I) package
- High power dissipation

APPLICATIONS

- For audio power amplifier and general purpose applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |



Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 140 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 140 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 10 | A |
| I _B | Base current | | 2 | A |
| P _T | Total power dissipation | T _C =25°C | 100 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

Silicon NPN Power Transistors

2SC2706

CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =25mA, I _B =0 | 140 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA, I _C =0 | 5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =5A; I _B =0.5A | | | 2.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =140V; I _E =0 | | | 10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V; I _C =0 | | | 10 | μA |
| h _{FE-1} | DC current gain | I _C =1A; V _{CE} =5V | 55 | | 160 | |
| h _{FE-2} | DC current gain | I _C =5A; V _{CE} =5V | 35 | | | |
| f _T | Transition frequency | I _C =1A; V _{CE} =5V | | 90 | | MHz |

Silicon NPN Power Transistors

2SC2706

PACKAGE OUTLINE

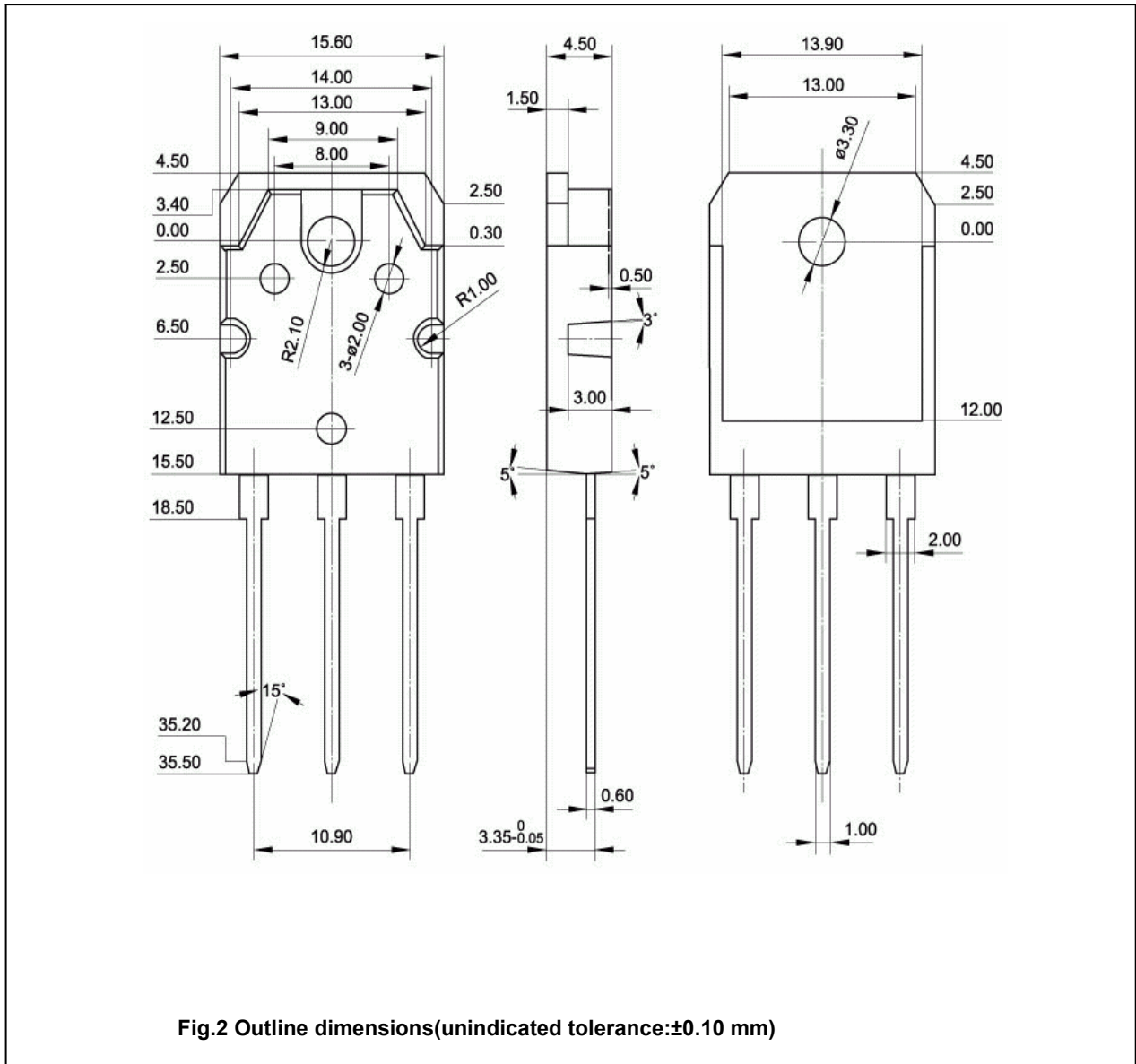


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)